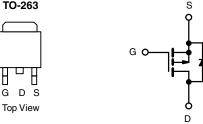


**Vishay Siliconix** 

# Automotive P-Channel 80 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	- 80				
$R_{DS(on)}(\Omega)$ at $V_{GS}$ = - 10 V	0.025				
$R_{DS(on)}(\Omega)$ at $V_{GS}$ = - 4.5 V	0.031				
I <sub>D</sub> (A)	- 50				
Configuration	Single				

### **TO-263**



P-Channel MOSFET

#### **FEATURES**

- TrenchFET<sup>®</sup> Power MOSFET
- Package with Low Thermal Resistance
- 100 %  $R_{\rm q}$  and UIS Tested
- AEC-Q101 Qualified<sup>d</sup>
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912



ORDERING INFORMATION				
Package	TO-263			
Lead (Pb)-free and Halogen-free	SQM50P08-25L-GE3			

<b>ABSOLUTE MAXIMUM RATINGS</b> ( $T_C = 25 \degree C$ , unless otherwise noted)						
PARAMETER	SYMBOL	LIMIT	UNIT			
Drain-Source Voltage		V <sub>DS</sub>	- 80	V		
Gate-Source Voltage		V <sub>GS</sub>	± 20	V		
Continuous Drain Current	T <sub>C</sub> = 25 °C <sup>a</sup>	I	- 50			
Continuous Drain Current	T <sub>C</sub> = 125 °C	I <sub>D</sub>	- 30			
Continuous Source Current (Diode Conduction) <sup>a</sup>	IS	- 50	А			
Pulsed Drain Current <sup>b</sup>	I <sub>DM</sub>	- 120				
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	- 47			
Single Pulse Avalanche Energy		E <sub>AS</sub>	110	mJ		
Martin an Dan an Director director	T <sub>C</sub> = 25 °C	P	150	W		
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 125 °C	P <sub>D</sub>	50	vv		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175	°C		

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-Ambient	PCB Mount <sup>c</sup>	R <sub>thJA</sub>	40	°C/W		
Junction-to-Case (Drain)		R <sub>thJC</sub>	1	C/W		

#### Notes

- a. Package limited.
- b. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.

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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static					•			
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, \text{ I}_{D} = -250 \mu\text{A}$		- 80	-	-	v	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	$V_{DS} = V_{GS}, I_D = -250 \ \mu A$		- 2.0	- 2.5		
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	± 100	nA	
		$V_{GS} = 0 V$	V <sub>DS</sub> = - 80 V	-	-	- 1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS} = 0 V$	$V_{DS} = -80 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$	-	-	- 50	μA	
		$V_{GS} = 0 V$	$V_{DS} = -80 \text{ V}, \text{ T}_{J} = 175 ^{\circ}\text{C}$	-	-	- 250		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = - 10 V	$V_{DS} \le$ - 5 V	- 50	-	-	А	
		$V_{GS} = -10 V$	I <sub>D</sub> = - 12.5 A	-	0.020	0.025		
Drain Sauras On State Desistance?		$V_{GS} = - 10 V$	I <sub>D</sub> = - 12.5 A, T <sub>J</sub> = 125 °C	-	-	0.044		
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 12.5 A, T <sub>J</sub> = 175 °C	-	-	0.055	Ω	
		$V_{GS} = -4.5 V$	I <sub>D</sub> = - 10.5 A	-	0.025	0.031		
Forward Transconductanceb	9 <sub>fs</sub>	V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 12.5 A		-	36	-	S	
Dynamic <sup>b</sup>								
Input Capacitance	C <sub>iss</sub>			-	4280	5350		
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	$V_{GS} = 0 V$ $V_{DS} = -25 V$ , f = 1 MHz		356	445	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			-	240	300	1	
Total Gate Charge <sup>c</sup>	Qg			-	91	137	nC	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{GS} = -10 V$	$V_{DS}$ = - 40 V, $I_{D}$ = - 12.5 A	-	8.2	-		
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			-	24	-		
Gate Resistance	Rg	f = 1 MHz		1.4	2.99	4.5	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	11	17		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD}$ = - 40 V, R <sub>L</sub> = 3.2 $\Omega$ I <sub>D</sub> $\cong$ - 12.5 A, V <sub>GEN</sub> = - 10 V, R <sub>g</sub> = 1 $\Omega$		-	11	17	- ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	71	107		
Fall Time <sup>c</sup>	t <sub>f</sub>			-	16	24		
Source-Drain Diode Ratings and Char	acteristics <sup>b</sup>							
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	- 120	Α	
	V <sub>SD</sub>	I <sub>F</sub> =	-	- 0.86	- 1.5	V		

Notes

a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$ 

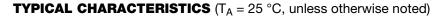
b. Guaranteed by design, not subject to production testing.

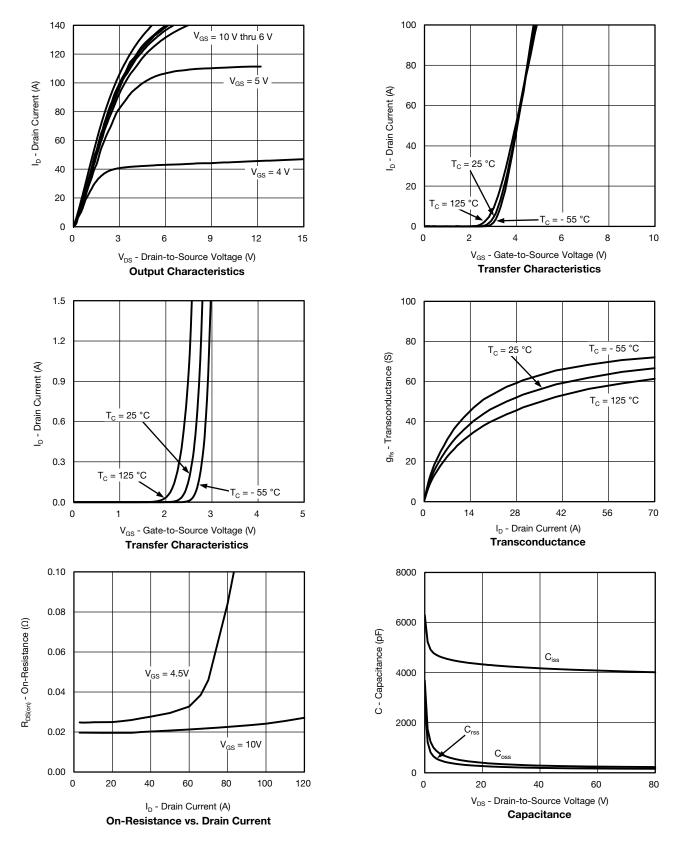
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



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S12-1847-Rev. B, 30-Jul-12

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Document Number: 67064

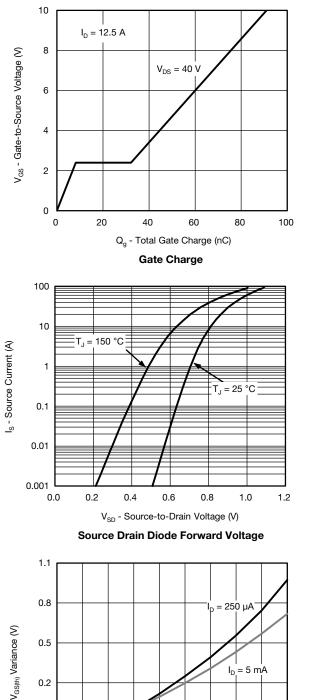
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SQM50P08-25L

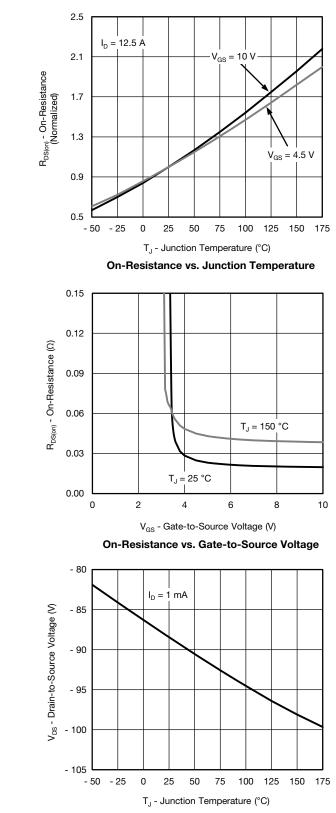
### **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)

www.vishay.com



T<sub>J</sub> - Temperature (°C)

**Threshold Voltage** 



Drain Source Breakdown vs. Junction Temperature

S12-1847-Rev. B, 30-Jul-12

-0.1

-0.4

- 50 - 25 0 25 50 75 100 125 150 175

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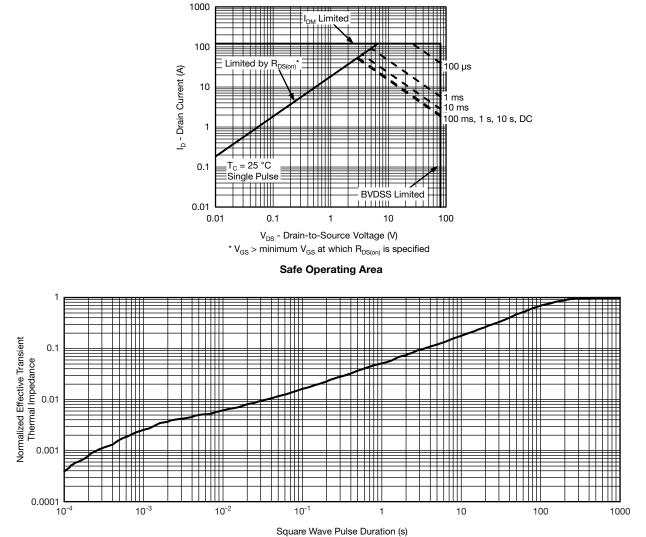
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### **THERMAL RATINGS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)

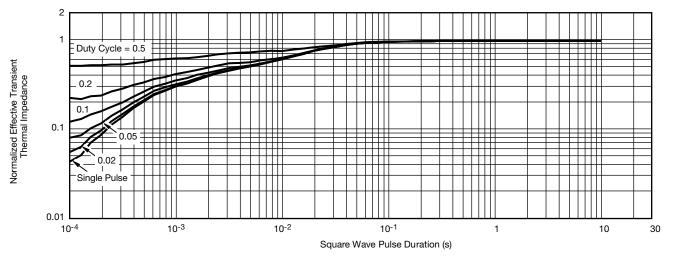


Normalized Thermal Transient Impedance, Junction-to-Ambient



### **Vishay Siliconix**

### **THERMAL RATINGS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

- The characteristics shown in the two graphs
- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="http://www.vishay.com/ppg267064">www.vishay.com/ppg267064</a>.



**Vishay Siliconix** 

TO-263 (D<sup>2</sup>PAK): 3-LEAD









DETAIL A (ROTATED 90°)



		INCHES		MILLIMETERS		
DIM.		MIN.	I. MAX. MIN.		MAX.	
A		0.160	0.190	4.064	4.826	
	b	0.020	0.020 0.039		0.990	
	b1	0.020	0.035	0.508	0.889	
	b2	0.045	0.055	1.143	1.397	
с*	Thin lead	0.013	0.018	0.330	0.457	
C	Thick lead	0.023	0.028	0.584	0.711	
c1	Thin lead	0.013	0.017	0.330	0.431	
CI	Thick lead	0.023	0.027	0.584	0.685	
	c2	0.045	0.055	1.143	1.397	
	D	0.340	0.380	8.636	9.652	
	D1	0.220	0.240	5.588	6.096	
	D2	0.038	0.042	0.965	1.067	
	D3	0.045	0.055	1.143	1.397	
	D4	0.044	0.052	1.118	1.321	
	E	0.380	0.410	9.652	10.414	
	E1	0.245	-	6.223	-	
E2		0.355	0.375	9.017	9.525	
E3		0.072	0.078	1.829	1.981	
	e 0.4		BSC	2.54	BSC	
	К	0.045	0.055	1.143	1.397	
	L	0.575	0.625	14.605	15.875	
	L1	0.090	0.110	2.286	2.794	
L2		0.040	0.055	1.016	1.397	
L3		0.050	0.070	1.270	1.778	
L4		0.010 BSC		0.254 BSC		
М		-	0.002	-	0.050	
ECN: T13-0707-Rev. K, 30-Sep-13 DWG: 5843						

#### Notes

- 1. Plane B includes maximum features of heat sink tab and plastic. 2. No more than 25 % of L1 can fall above seating plane by
- max. 8 mils.3. Pin-to-pin coplanarity max. 4 mils.
- 4. \*: Thin lead is for SUB, SYB.
  - Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

This feature is for thick lead.

Revison: 30-Sep-13



### **RECOMMENDED MINIMUM PADS FOR D<sup>2</sup>PAK: 3-Lead**



Recommended Minimum Pads Dimensions in Inches/(mm)

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